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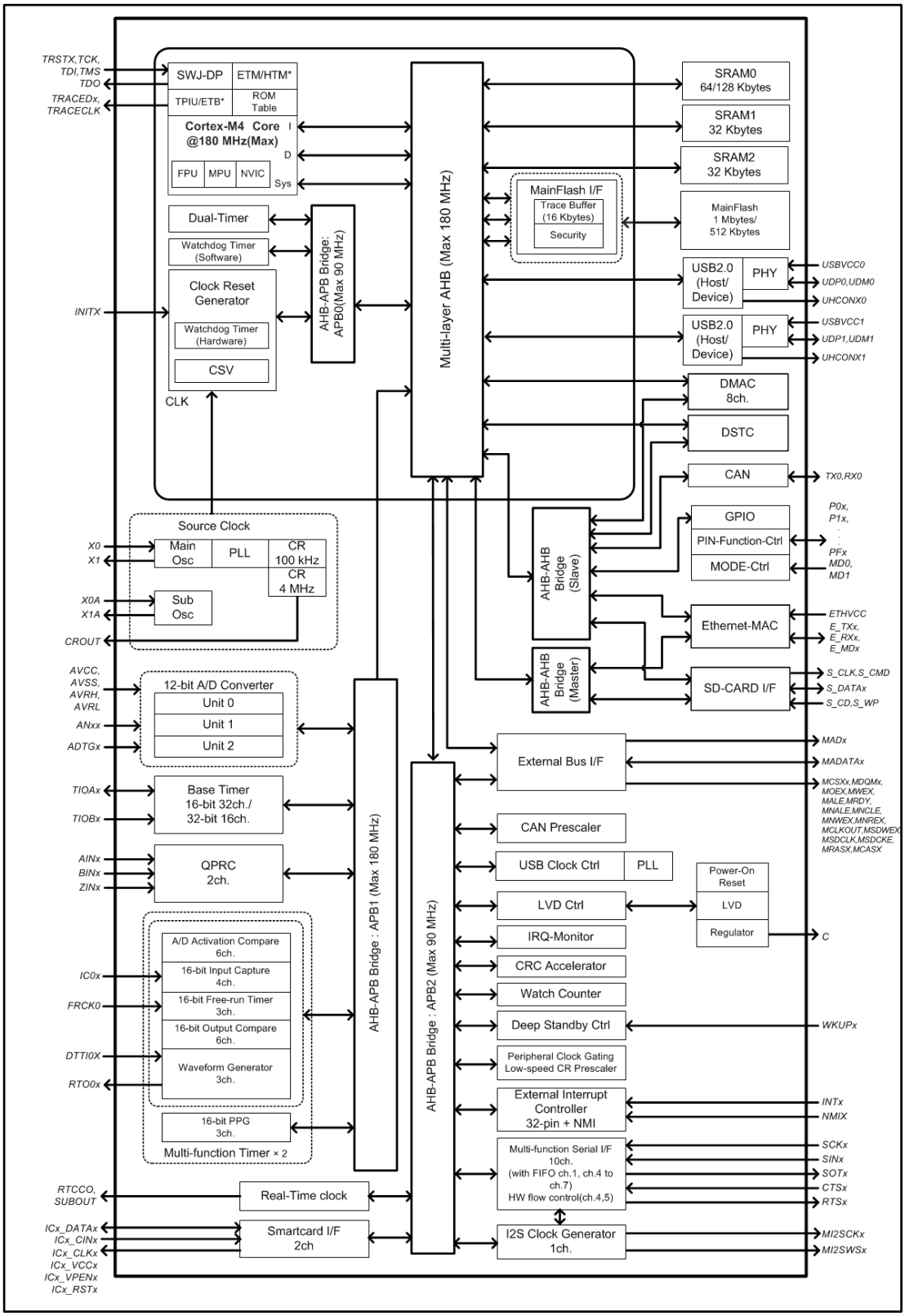
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CSIO, EBI/EMI, I²C, LINbus, SD, SmartCard, SPI, UART/USART, USB
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	121
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 24x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/s6e2gk6hhagv2000a

1. S6E2G Series Block Diagram



Description			Product Name				
			S6E2GM6 S6E2GM8	S6E2GK6 S6E2GK8	S6E2GH6 S6E2GH8	S6E2G36 S6E2G38	S6E2G26 S6E2G28
Base timer (PWC/Reload timer/PWM/PPG)			16 ch (Max)				
MF timer	A/D activation compare	6 ch	2 units (Max)				
	Input capture	4 ch					
	Free-run timer	3 ch					
	Output compare	6 ch					
	Waveform generator	3 ch					
	PPG	3 ch					
Smartcard (ISO7816)			2 ch (Max)				
QPRC			2 ch (Max)				
Dual timer			1 unit				
Real-time clock			1 unit				
Watch counter			1 unit				
CRC accelerator			Yes (fixed)				
Watchdog timer			1 ch (SW) + 1 ch (HW)				
External interrupts			32 pins (Max)+ NMI × 1				
CSV (clock supervisor)			Yes				
LVD (low-voltage detector)			2 ch				
Built-in CR	High-speed		4 MHz				
	Low-speed		100 kHz				
Debug function			SWJ-DP/ETM/HTM				
Unique ID			Yes				

*1: Crypto Assist Function is built in following products.
S6E2GM6HHA, S6E2GM8HHA, S6E2GM6JHA, S6E2GM8JHA

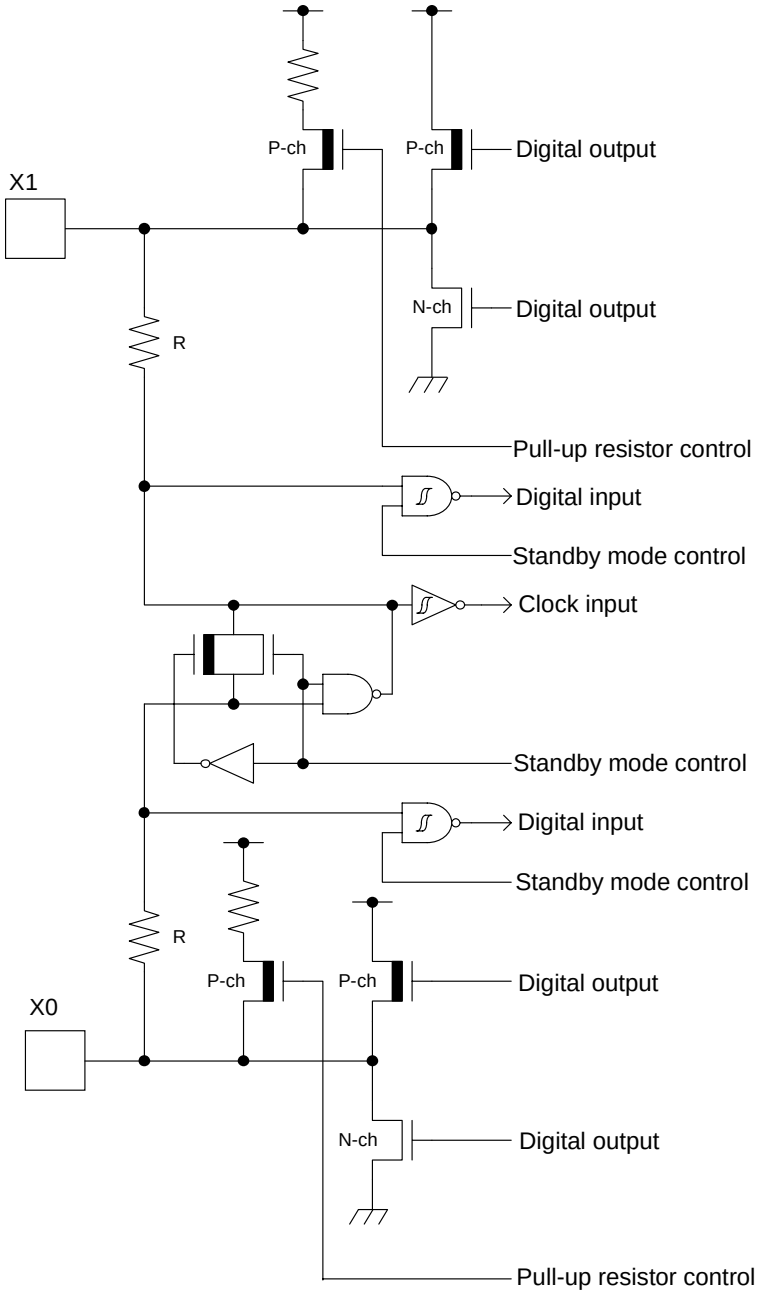
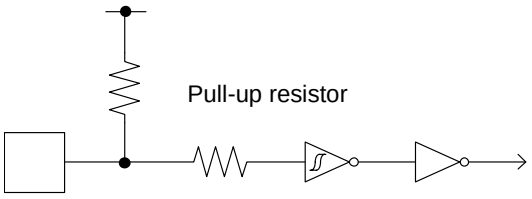
Notes:

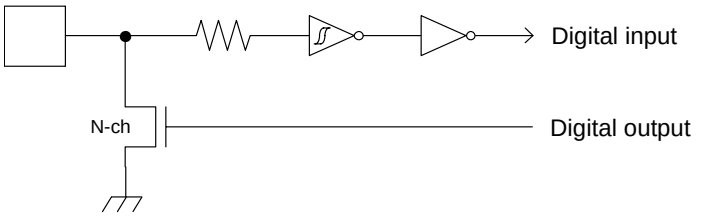
- *Because of package pin limitations, not all functions within the device can be brought out to external pins. You must carefully work out the pin allocation needed for your design.*
  You must use the port relocate function of the I/O port according to your function use.
- *See 12.4.3 Built-In CR Oscillation Characteristics for the accuracy of the built-in CR.*

Pin Number		Pin Name	I/O Circuit Type	Pin State Type
LQFP-176	LQFP-144			
127	103	P21	I	K
		ADTG_4		
		SIN0_0		
		INT27_0		
		CROUT_0		
128	104	P20	I	F
		NMIX		
		WKUP0		
129	105	USBVCC1	-	-
130	106	P82	H	R
		UDM1		
131	107	P83	H	R
		UDP1		
132	108	VSS	-	-
133	109	VCC	-	-
134	110	P00	E	G
		TRSTX		
135	111	P01	E	G
		TCK		
		SWCLK		
136	112	P02	E	G
		TDI		
137	113	P03	E	G
		TMS		
		SWDIO		
138	114	P04	E	G
		TDO		
		SWO		
139	-	P90	E	K
		RTO10_1 (PPG10_1)		
		TIOB0_1		
		INT12_1		
		IC0_CLK_1		
140	-	P91	E	K
		SIN5_1		
		RTO11_1 (PPG11_1)		
		TIOB1_1		
		INT13_1		
		IC0_VCC_1		

Pin Number		Pin Name	I/O Circuit Type	Pin State Type
LQFP-176	LQFP-144			
141	-	P92	E	K
		SOT5_1 (SDA5_1)		
		RTO12_1 (PPG12_1)		
		TIOB2_1		
		INT14_1		
		IC0_VPEN_1		
142	-	P93	E	K
		SCK5_1 (SCL5_1)		
		RTO13_1 (PPG13_1)		
		TIOB3_1		
		INT15_1		
		IC0_RST_1		
143	-	P94	E	I
		CTS5_1		
		RTO14_1 (PPG14_1)		
		TIOB4_1		
		IC0_DATA_1		
144	-	P95	E	I
		RTS5_1		
		RTO15_1 (PPG15_1)		
		TIOB5_1		
		IC0_CIN_1		
145	115	PC0	K	V
		E_RXER		
146	116	PC1	K	V
		TIOB6_0		
		E_RX03		
147	117	PC2	K	V
		TIOA6_0		
		E_RX02		
148	118	PC3	K	V
		TIOB7_0		
		E_RX01		
149	119	PC4	K	V
		TIOA7_0		
		E_RX00		
150	120	PC5	K	V
		TIOB14_0		
		E_RXDV		

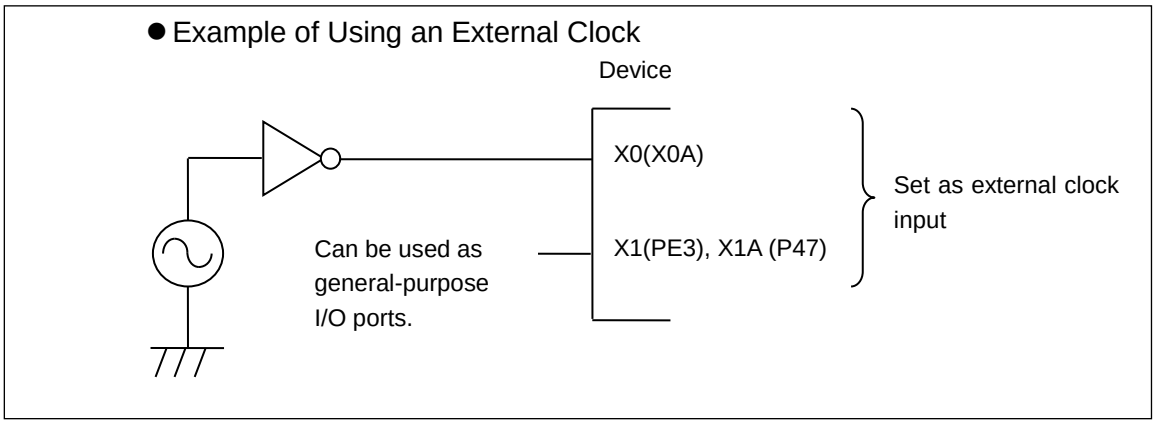
7. I/O Circuit Type

Type	Circuit	Remarks
A		It is possible to select the main Oscillation/GPIO function. When the main oscillation is selected: ・ Oscillation feedback resistor: approximately 1 MΩ ・ Standby mode control When the GPIO is selected: ・ CMOS level output. ・ CMOS level hysteresis input ・ Pull-up resistor control ・ Standby mode control ・ Pull-up resistor: approximately 50 kΩ ・ I_{OH} = -4 mA, I_{OL} = 4 mA
B		・ CMOS level hysteresis input ・ Pull-up resistor: approximately 50 kΩ

Type	Circuit	Remarks
C		・ Open drain output ・ CMOS level hysteresis input

Using an External Clock

When using an external clock as an input of the main clock, set X0/X1 to the external clock input, and input the clock to X0. X1(PE3) can be used as a general-purpose I/O port. Similarly, when using an external clock as an input of the sub clock, set X0A/X1A to the external clock input and input the clock to X0A. X1A (P47) can be used as a general-purpose I/O port.

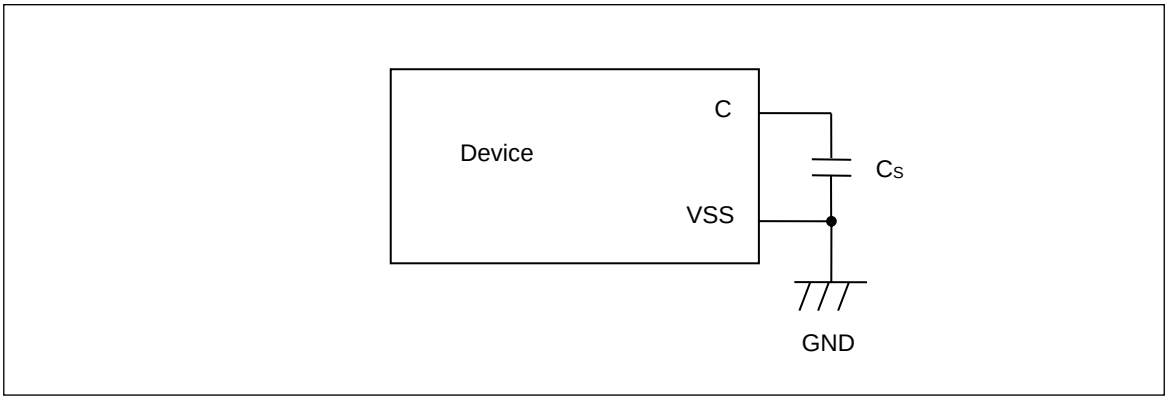


Handling When Using Multi-Function Serial Pin as I²C Pin

If the application uses the multi-function serial pin as an I²C pin, the P-channel transistor of the digital output must be disabled. I²C pins need to conform to electrical limitations like other pins, however, and avoid connecting to live external systems with the MCU power off.

C Pin

Devices in this series contain a regulator. Be sure to connect a smoothing capacitor (C_S) for the regulator between the C pin and the GND pin. Please use a ceramic capacitor or a capacitor of equivalent frequency characteristics as a smoothing capacitor. Some laminated ceramic capacitors have a large capacitance variation due to thermal fluctuation. Please select a capacitor that meets the specifications in the operating conditions to use by evaluating the temperature characteristics of the device. A smoothing capacitor of about 4.7 µF would be recommended for this series.



Mode Pins (MD0)

Connect the MD pin (MD0) directly to VCC or VSS pins. Design the printed circuit board such that the pull-up/down resistance stays low, the distance between the mode pins and VCC pins or VSS pins is as short as possible, and the connection impedance is low when the pins are pulled up/down such as for switching the pin level and rewriting the flash memory data. This is important to prevent the device from erroneously switching to test mode as a result of noise.

11. Pin Status in Each CPU State

The terms used for pin status have the following meanings:

- INITX = 0

  This is the period when the INITX pin is at the L level.

- INITX = 1

  This is the period when the INITX pin is at the H level.

- SPL = 0

  This is the status that the standby pin level setting bit (SPL) in the standby mode control register (STB_CTL) is set to 0.

- SPL = 1

  This is the status that the standby pin level setting bit (SPL) in the standby mode control register (STB_CTL) is set to 1.

- Input enabled

  Indicates that the input function can be used.

- Internal input fixed at 0

  This is the status that the input function cannot be used. Internal input is fixed at L.

- Hi-Z

  Indicates that the pin drive transistor is disabled and the pin is put in the Hi-Z state.

- Setting disabled

  Indicates that the setting is disabled.

- Maintain previous state

  Maintains the state that was immediately prior to entering the current mode.
  If a built-in peripheral function is operating, the output follows the peripheral function.
  If the pin is being used as a port, that output is maintained.

- Analog input is enabled

  Indicates that the analog input is enabled.

- Trace output

  Indicates that the trace function can be used.

- GPIO selected

  In Deep standby mode, pins switch to the general-purpose I/O port.

- Setting prohibition

  Prohibition of a setting by specification limitation

Package thermal resistance and maximum permissible power for each package are shown below.
The operation is guaranteed maximum permissible power or less for semiconductor devices.

Table for Package Thermal Resistance and Maximum Permissible Power

Package	Printed Circuit Board	Thermal Resistance θja (°C/W)	Maximum Permissible Power (mW)	
			T_A = +85 °C	T_A = +105 °C
LQS144 (0.5-mm pitch)	Single-layered both sides	48	833	417
	4 layers	33	1212	606
LQP176 (0.5-mm pitch)	Single-layered both sides	45	889	444
	4 layers	31	1290	645

WARNING:

- *The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.*
  Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.
- *No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet.*
  Users considering application outside the listed conditions are advised to contact their representatives beforehand.

12.3 DC Characteristics

12.3.1 Current Rating

Table 12-1 Typical and Maximum Current Consumption in Normal Operation (PLL), Code Running from Flash Memory (Flash Accelerator Mode and Trace Buffer Function Enabled)

Parameter	Symbol	Pin Name	Conditions		Frequency*4	Value		Unit	Remarks
						Typ*1	Max*2		
Power supply current	I_{CC}	VCC	Normal operation *7,*8 (PLL)	*5	180 MHz	73	131	mA	*3 When all peripheral clocks are on
				*6	160 MHz	65	123	mA	
					144 MHz	59	117	mA	
					120 MHz	50	108	mA	
					100 MHz	43	101	mA	
					80 MHz	35	93	mA	
					60 MHz	27	85	mA	
					40 MHz	19	77	mA	
					20 MHz	11	69	mA	
					8 MHz	6.9	64	mA	
					4 MHz	5.3	63	mA	
				*5	180 MHz	44	102	mA	*3 When all peripheral clocks are off
				*6	160 MHz	40	98	mA	
					144 MHz	36	94	mA	
					120 MHz	31	89	mA	
					100 MHz	27	85	mA	
					80 MHz	22	80	mA	
					60 MHz	17	75	mA	
					40 MHz	13	71	mA	
					20 MHz	7.9	65	mA	
					8 MHz	5.2	63	mA	
					4 MHz	4.3	62	mA	

1: T_A = +25 °C, V_{CC} = 3.3 V

2: T_J = +125 °C, V_{CC} = 5.5 V

3: When all ports are input and are fixed at 0

4: Frequency is a value of HCLK when PCLK0 = PCLK1 = PCLK2 = HCLK/2

5: When operating flash accelerator mode and trace buffer function (FRWTR.RWT = 11, FBFCR.BE = 1)

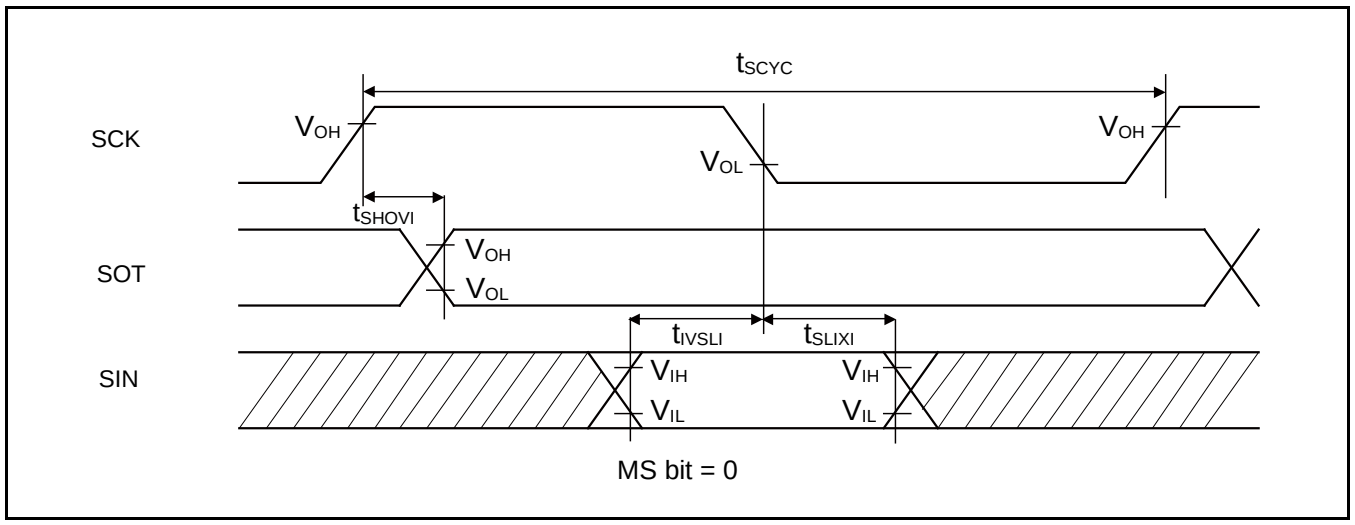
6: When operating flash accelerator mode and trace buffer function (FRWTR.RWT = 10, FBFCR.BE = 1)

7: Firmware being executed during data collection for this table is not being accessed from the MainFlash memory."

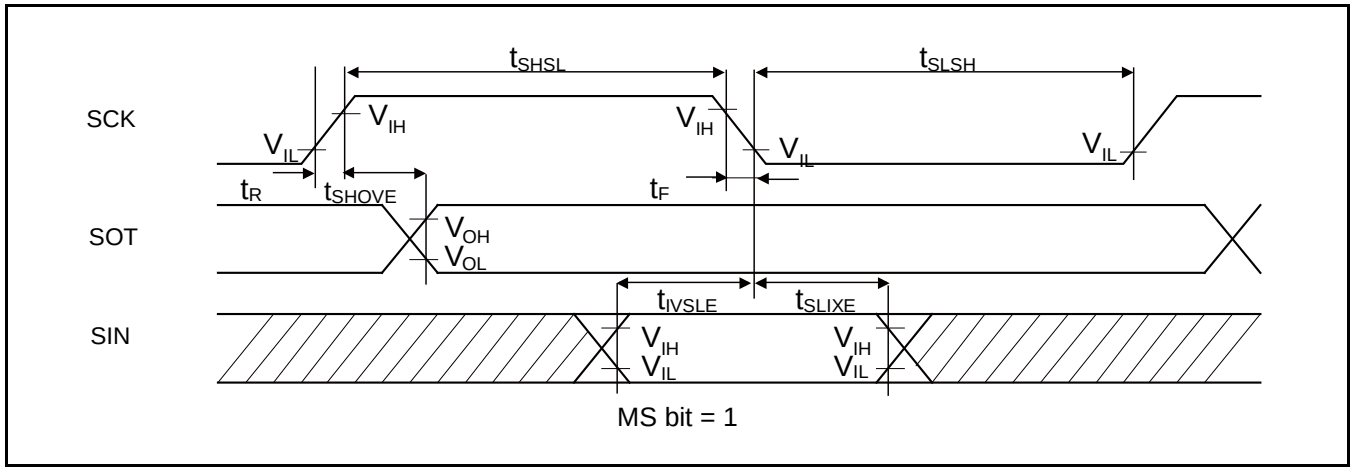
8: When using the crystal oscillator of 4 MHz (including the current consumption of the oscillation circuit)

Parameter	Symbol	Pin Name	Conditions	Value			Unit	Remarks
				Min	Typ	Max		
L level output voltage	V_{OL}	4 mA type	$V_{CC} \geq 4.5$ V, I_{OL} = 4 mA	V_{SS}	-	0.4	V	
			$V_{CC} < 4.5$ V, I_{OL} = 2 mA					
			$ETHV_{CC} \geq 4.5$ V, I_{OL} = 4 mA	V_{SS}	-	0.4	V	
			$RTHV_{CC} < 4.5$ V, I_{OL} = 2 mA					
		8 mA type	$V_{CC} \geq 4.5$ V, I_{OL} = 8 mA	V_{SS}	-	0.4	V	
			$V_{CC} < 4.5$ V, I_{OL} = 4 mA					
			$ETHV_{CC} \geq 4.5$ V, I_{OL} = 8 mA	V_{SS}	-	0.4	V	
			$RTHV_{CC} < 4.5$ V, I_{OL} = 4 mA					
		12 mA type	$V_{CC} \geq 4.5$ V, I_{OL} = 12 mA	V_{SS}	-	0.4	V	
			$V_{CC} < 4.5$ V, I_{OL} = 8 mA					
		The pin doubled as USB I/O	$USBV_{CC} \geq 4.5$ V, I_{OL} = 18.5 mA	V_{SS}	-	0.4	V	*1
			$USBV_{CC} < 4.5$ V, I_{OL} = 10.5 mA					
		The pin doubled as I^2C Fm+	$V_{CC} \geq 4.5$ V, I_{OL} = 4 mA	V_{SS}	-	0.4	V	At GPIO
			$V_{CC} < 4.5$ V, I_{OL} = 3 mA					
			$V_{CC} \leq 4.5$ V, I_{OL} = 20 mA					At I^2C Fm+
Input leak current	I_{IL}	-	-	- 5	-	+ 5	µA	
Pull-up resistor value	R_{PU}	Pull-up pin	$V_{CC} \geq 4.5$ V	25	50	100	kΩ	
			$V_{CC} < 4.5$ V	30	80	200		
Input capacitance	C_{IN}	Other than VCC, USBVCC0, USBVCC1, ETHVCC, VSS, AVCC, AVSS, AVRH	-	-	5	15	pF	

1: $USBV_{CC}0$ and $USBV_{CC}1$ are described as $USBV_{CC}$.



MS bit = 0



MS bit = 1

When Using Synchronous Serial Chip Select (SCINV = 1, CSLVL = 1)

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V)

Parameter	Symbol	Conditions	V_{CC} < 4.5 V		V_{CC} ≥ 4.5 V		Unit
			Min	Max	Min	Max	
SCS↓→SCK↓ setup time	t_{CSSI}	Internal shift clock operation	(*1)-50	(*1)+0	(*1)-50	(*1)+0	ns
SCK↑→SCS↑ hold time	t_{CSHI}		(*2)+0	(*2)+50	(*2)+0	(*2)+50	ns
SCS deselect time	t_{CSDI}		(*3)-50 +5t_{CYCP}	(*3)+50 +5t_{CYCP}	(*3)-50 +5t_{CYCP}	(*3)+50 +5t_{CYCP}	ns
SCS↓→SCK↓ setup time	t_{CSSE}	External shift clock operation	3t_{CYCP}+30	-	3t_{CYCP}+30	-	ns
SCK↑→SCS↑ hold time	t_{CSHE}		0	-	0	-	ns
SCS deselect time	t_{CSDE}		3t_{CYCP}+30	-	3t_{CYCP}+30	-	ns
SCS ↓ →SOT delay time	t_{DSE}		-	40	-	40	ns
SCS ↑ →SOT delay time	t_{DEE}		0	-	0	-	ns

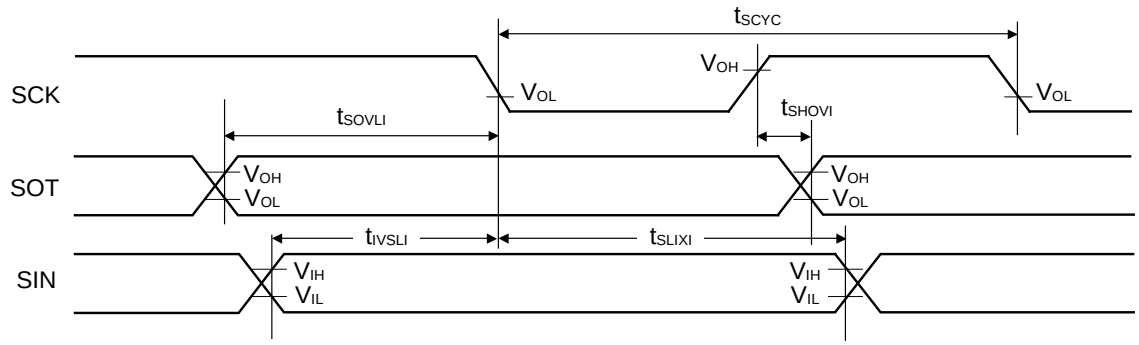
(*1): CSSU bit value×serial chip select timing operating clock cycle [ns]

(*2): CSHD bit value×serial chip select timing operating clock cycle [ns]

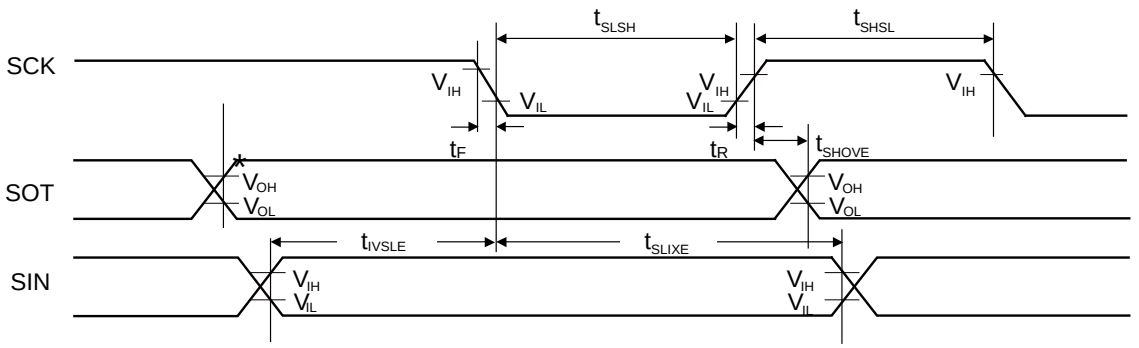
(*3): CSDS bit value×serial chip select timing operating clock cycle [ns]

Notes:

- *t_{CYCP} indicates the APB bus clock cycle time. For more information about the APB bus number to which the multi-function serial is connected, see 1. S6E2G Series Block Diagram in this data sheet.*
- *For more information about CSSU, CSHD, CSDS, and the serial chip select timing operating clock, see FM4 Family Peripheral Manual Main Part (002-04856).*
- *When the external load capacitance C_L = 30 pF.*



MS bit = 0



MS bit = 1

*: Changes when writing to TDR register

12.4.13 External Input Timing

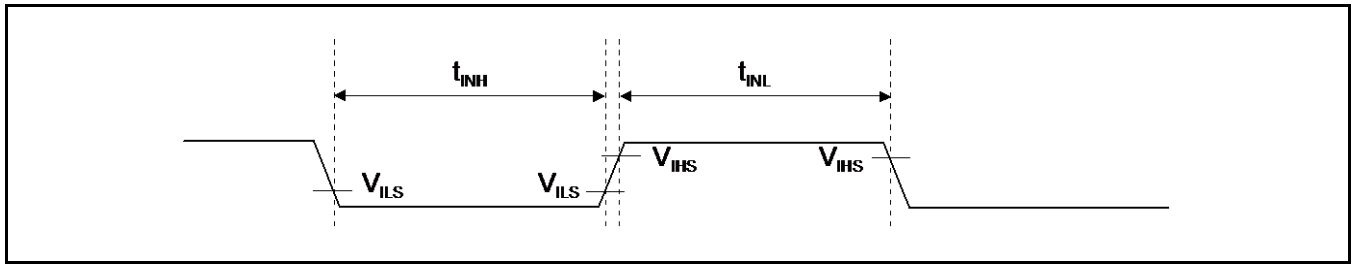
(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V)

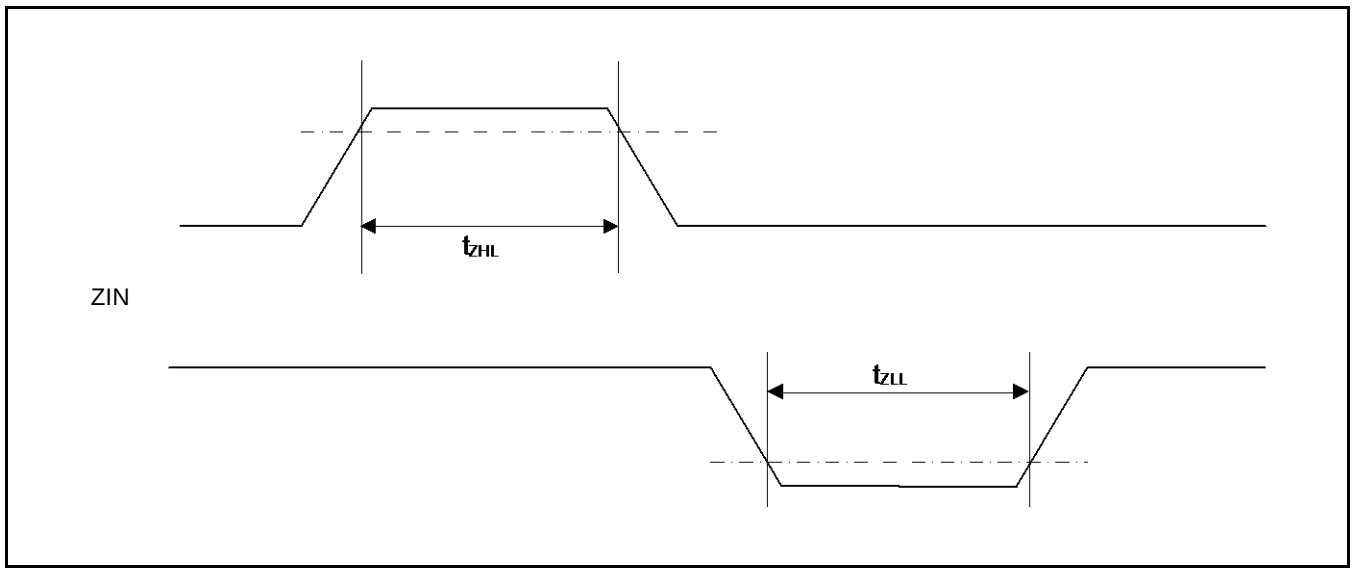
Parameter	Symbol	Pin Name	Conditions	Value		Unit	Remarks
				Min	Max		
Input pulse width	t_{INH}, t_{INL}	ADTGx	-	$2t_{CYCP}$*1	-	ns	A/D converter trigger input
		FRCKx					Free-run timer input clock
		Icxx					Input capture
		DTTIxX	-	$2t_{CYCP}$*1	-	ns	Waveform generator
		INT00 to INT31, NMIX	-	$2t_{CYCP}$ + 100*1	-	ns	External interrupt, NMI
				500*2	-	ns	
		WKUPx	-	500*3	-	ns	Deep standby wake up

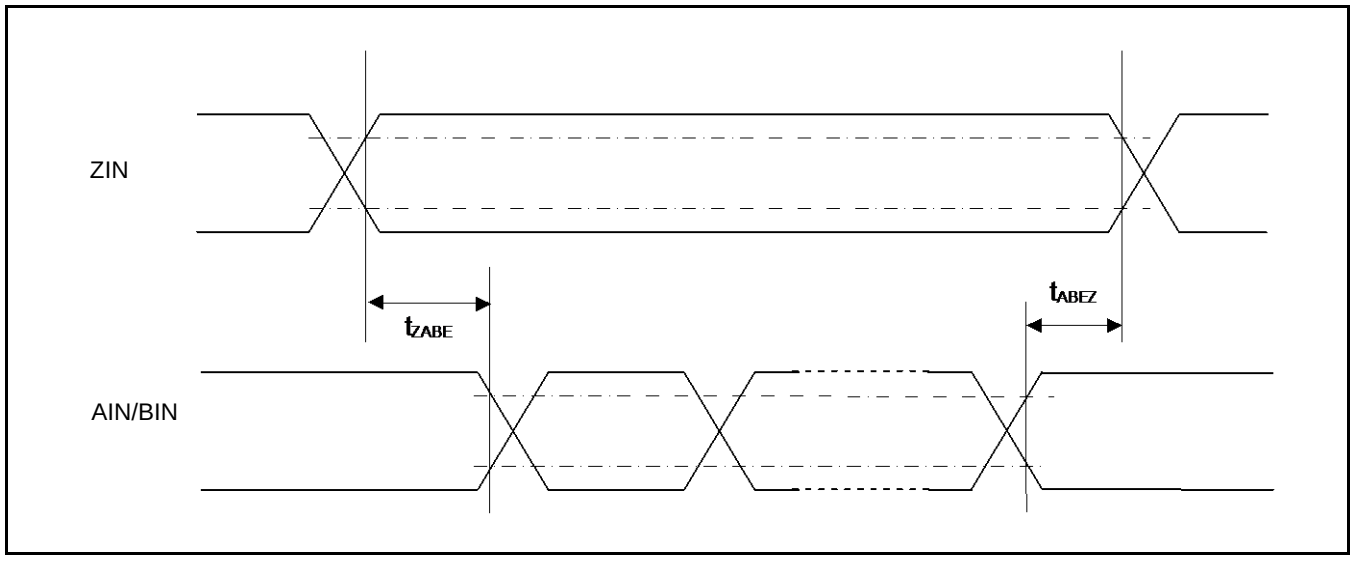
1: t_{CYCP} indicates the APB bus clock cycle time except stop when in Stop mode, in Timer mode. For more information about the APB bus number to which the A/D converter, multi-function timer, and external interrupt are connected, see 1. S6E2G Series Block Diagram in this data sheet.

2: When in Stop mode, in Timer mode

3: When in Deep Standby RTC mode, in Deep Standby Stop mode




ZIN
tZHL
tZLL


ZIN
tZABE
tABEZ
AIN/BIN

12.8 MainFlash Memory Write/Erase Characteristics

(V_{CC} = 2.7V to 5.5V)

Parameter		Value			Unit	Remarks
		Min	Typ	Max		
Sector erase time	Large Sector	-	0.7	3.7	s	Includes write time prior to internal erase
	Small Sector	-	0.3	1.1	s	
Half word (16-bit) write time	Write cycles ≤ 100 times	-	12	100	µs	Not including system-level overhead time
	Write cycles > 100 times			200		
Chip erase time*		-	13.6	68	s	Includes write time prior to internal erase

*: It indicates the chip erase time of 1MB MainFlash memory

For devices with 1.5 MB or 2 MB of MainFlash memory, two erase cycles are required.

See 3.2.2 Command Operating Explanations and 3.3.3 Flash Erase Operation in this product's Flash Programming Manual for the detail.

Write Cycles and Data Retention Time

Erase/Write Cycles (Cycle)	Data Retention Time (Year)
1,000	20*
10,000	10*
100,000	5*

*: This value comes from the technology qualification (using Arrhenius equation to translate high temperature acceleration test result into average temperature value at + 85°C).

12.9 Standby Recovery Time

12.9.1 Recovery Cause: Interrupt/WKUP

The time from the interrupt occurring to the time of program operation start is shown.

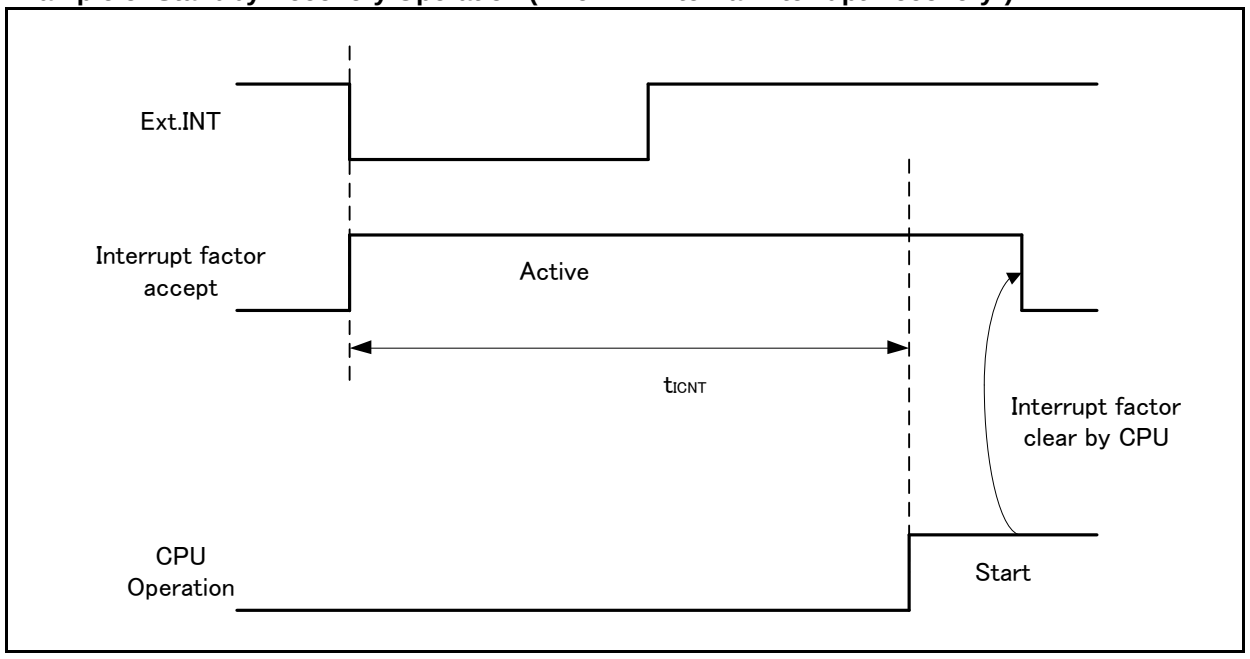
Recovery Count Time

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V)

Parameter	Symbol	Value		Unit	Remarks
		Typ	Max*		
Sleep mode	t_{ICNT}	HCLK×1		µs	
High-speed CR Timer mode Main Timer mode PLL Timer mode		40	80	µs	
Low-speed CR Timer mode		450	900	µs	
Sub Timer mode		896	1136	µs	
RTC mode Stop mode (High-speed CR/Main/PLL Run mode return)		316	581	µs	
RTC mode Stop mode (Low-speed CR/sub Run mode return)		270	540	µs	
Deep Standby RTC mode with RAM retention		365	667	µs	without RAM retention
Deep Standby Stop mode with RAM retention		365	667	µs	with RAM retention

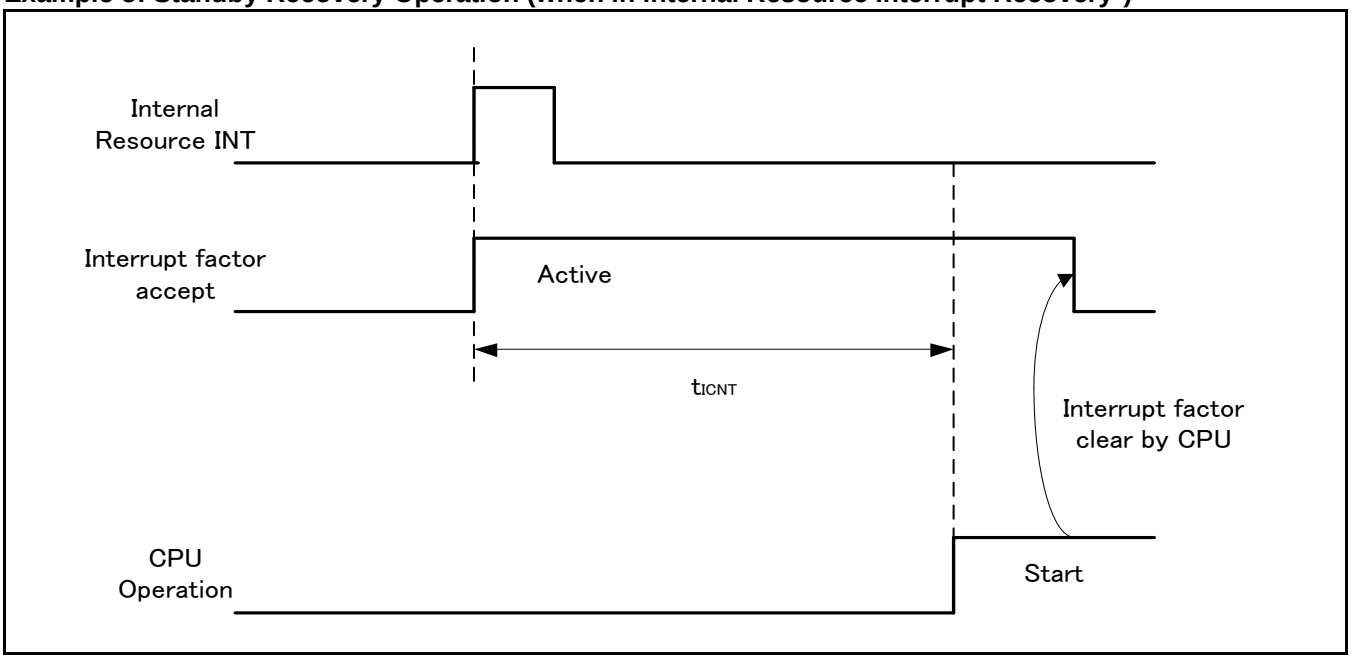
*: The maximum value depends on the built-in CR accuracy.

Example of Standby Recovery Operation (when in External Interrupt Recovery*)



*: External interrupt is set to detecting fall edge.

Example of Standby Recovery Operation (when in Internal Resource Interrupt Recovery*)



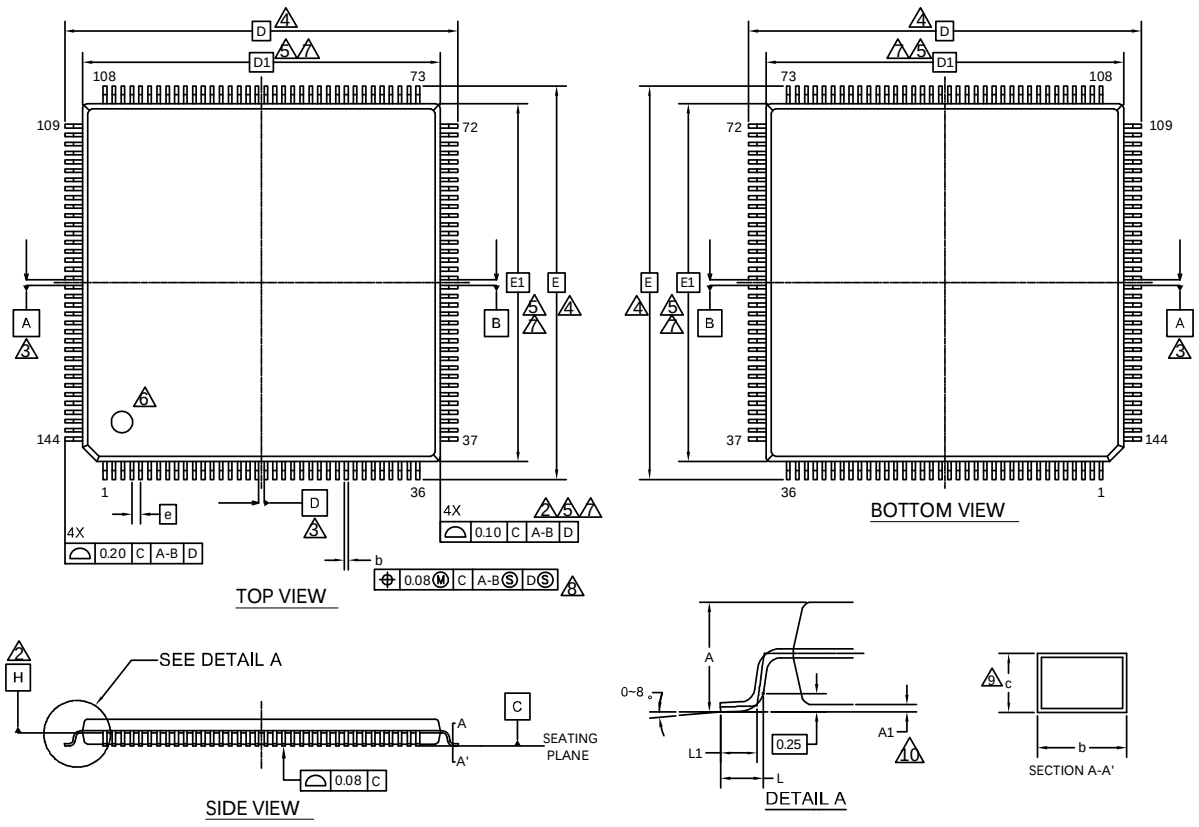
*: Depending on the standby mode, interrupt from the internal resource is not included in the recovery cause.

Notes:

- *The return factor is different in each low-power consumption mode. See Chapter 6: Low Power Consumption mode and Operations of Standby modes in FM4 Family Peripheral Manual Main Part (002-04856).*
- *The recovery process is unique for each operating mode. See Chapter 6: Low Power Consumption mode in FM4 Family Peripheral Manual Main Part (002-04856).*

14. Package Dimensions

Package Type	Package Code
LQFP 144	LQS144



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	—	—	1.70
A1	0.05	—	0.15
b	0.17	0.22	0.27
c	0.09	—	0.20
D		22.00 BSC	
D1		20.00 BSC	
e		0.50 BSC	
E		22.00 BSC	
E1		20.00 BSC	
L	0.45	0.60	0.75
L1	0.30	0.50	0.70

NOTES

1. ALL DIMENSIONS ARE IN MILLIMETERS
2. DATUM PLANE H IS LOCATED AT THE BOTTOM OF THE MOLD PARTING LINE COINCIDENT WITH WHERE THE LEAD EXITS THE BODY.
3. DATUMS A-B AND D TO BE DETERMINED AT DATUM PLANE H.
4. TO BE DETERMINED AT SEATING PLANE C.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25mm PRE SIDE. DIMENSIONS D1 AND E1 INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
6. DETAILS OF PIN 1 IDENTIFIER ARE OPTIONAL BUT MUST BE LOCATED WITHIN THE ZONE INDICATED.
7. REGARDLESS OF THE RELATIVE SIZE OF THE UPPER AND LOWER BODY SECTIONS. DIMENSIONS D1 AND E1 ARE DETERMINED AT THE LARGEST FEATURE OF THE BODY EXCLUSIVE OF MOLD FLASH AND GATE BURRS. BUT INCLUDING ANY MISMATCH BETWEEN THE UPPER AND LOWER SECTIONS OF THE MOLDER BODY.
8. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. THE DAMBAR PROTRUSION (S) SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED b MAXIMUM BY MORE THAN 0.08mm. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE LEAD FOOT.
9. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.10mm AND 0.25mm FROM THE LEAD TIP.
10. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.

PACKAGE OUTLINE, 144 LEAD LQFP
20.0X20.0X1.7 MM LQS144 REV*A

002-13015 *A